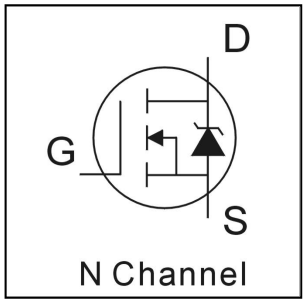
Gunter Semiconductor GmbH | GLC110

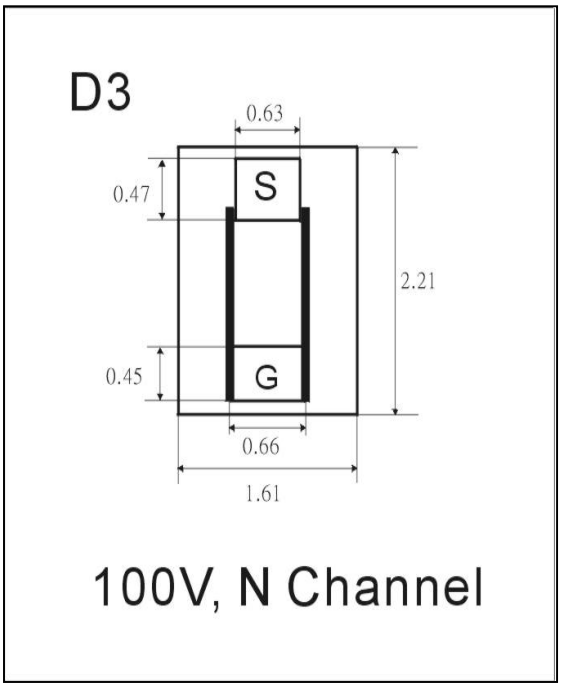
N Channel Power MOSFET FOR LOGIC DRIVER

Chip Specification



General Description:

* Advanced Process Technology
* Dynamic dv/dt Rating
* **175℃ Operating Temperature**
* **Fast Switching**
* **Fully Avalanche Rated**
* **RDS(ON) rated at VGS = 5V**
* **Ease of parallel**



Mechanical Data:

D3	
Dimension	**1.61mm x 2.21mm**
Thickness:	**400 μm**
Metallization**:**	
Top :	: **Al**
Backside :	**CrNiAg / Au**
Suggested Bonding Conditions:	
Die Mounting:	**Solder Perform**
95/5 PbSn or 92.5./2.5/5 PbAgIn	
Source Bonding Wire**:**	**5 mil Al**

Absolute Maximum Rating @Ta=25℃

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	100	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.54	Ω	VGS=5V, ID=3.45A
Continuous Drain current (in target package)	ID@25℃	5.6	A	VGS= 5V
Continuous Drain current (in target package)	ID@100℃	4	A	VGS= 5V
Operation Junction Temperature	Tj	-55~175	℃	
Storage Temperature	TSTR	-55~175	℃	

Target Device: IRL510

TO-220AB	PD	43	W	@Tc=25℃